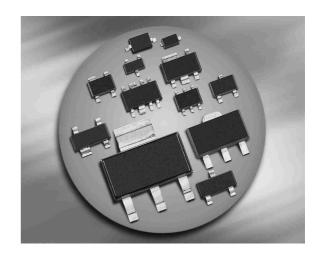


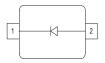
Silicon Variable Capacitance Diode

- For VHF tuned circuit applications
- High figure of merit
- Pb-free (RoHS compliant) package





BB439



Туре	Package	Configuration	L S(nH)	Marking
BB439	SOD323	single	1.8	white 2

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit V	
Diode reverse voltage	V_{R}	28		
Peak reverse voltage	V_{RM}	30		
$(R \ge 5k\Omega)$				
Forward current	I _F	20	mA	
Operating temperature range	T_{op}	-55 125	°C	
Storage temperature	$T_{ m stg}$	-55 150		

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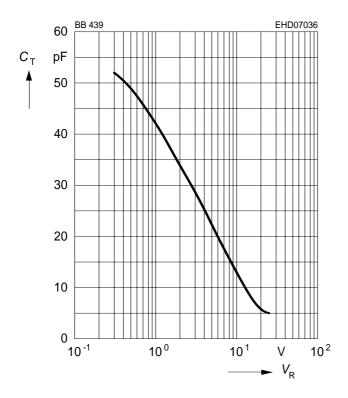
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol		Values		
		min.	typ.	max.	
DC Characteristics	·	•	•		•
Reverse current	I_{R}				nA
<i>V</i> _R = 28 V		-	-	20	
$V_{R} = 28 \text{ V}, T_{A} = 85 ^{\circ}\text{C}$		-	-	200	
AC Characteristics					
Diode capacitance	C _T				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		-	43	-	
$V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$		31.5	34.5	37.5	
$V_{R} = 3 \text{ V}, f = 1 \text{ MHz}$		26.5	29	31.5	
V_{R} = 25 V, f = 1 MHz		4.3	5.1	6	
Capacitance ratio	C _{T2} /C _{T25}	6	6.9	8	
V_{R} = 2 V, V_{R} = 25 V, f = 1 MHz					
Capacitance ratio	C_{T3}/C_{T25}	5	5.8	6.5	
V_{R} = 3 V, V_{R} = 25 V, f = 1 MHz					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	3	%
$V_{R} = 3 \text{ V}, V_{R} = 25 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	$r_{\rm S}$	-	0.35	0.5	Ω
<i>V</i> _R = 10 V, <i>f</i> = 100 MHz					
Figure of merit	Q				
$V_{R} = 3 \text{ V}, f = 50 \text{ MHz}$		-	280	-	
V_{R} = 25 V, f = 200 MHz		-	600	_	

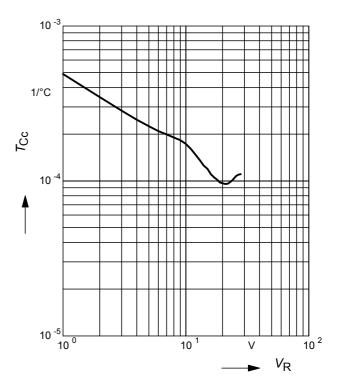
¹For details please refer to Application Note 047.



Diode capacitance $C_T = f(V_R)$ f = 1MHz



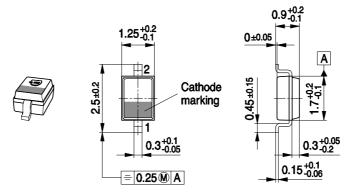
Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



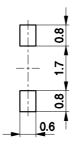
3 2011-06-15



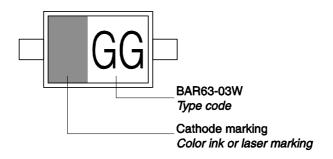
Package Outline



Foot Print

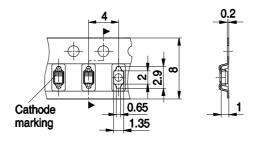


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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